

Notice of References Cited

Application/Control No.

09/605,293

Applicant(s)/Patent Under
Reexamination
CHAPEK, DAVID L.

Examiner

JAY C. KIM

Art Unit

2815

Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,143,631 A	11-2000	Chapek, David L.	438/513
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Hosaka et al., "Impurity contamination of the SiO ₂ layer on Si wafers during ion etching", Journal of Vacuum Science and Technology 18 (1981) pp. 17-22.
	V	Magnuson et al., "High Efficiency Source for Metal Ions", The Review of Scientific Instruments 36 (1965) pp. 136-142.
	W	Matsuda et al., "Ion species measurement of high current metal ion beams extracted from a multicusp ion source", Review of Scientific Instruments 63 (1992) pp. 2481-2483.
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(s).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.